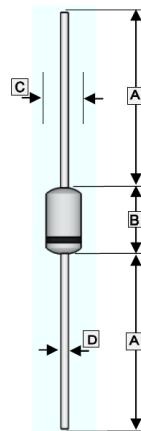


RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

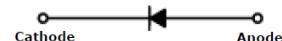
FEATURES

- DO-34 Package (JEDEC DO-204)
- Through-Hole Device Type Mounting
- Hermetically Sealed Glass
- Compression Bonded Construction
- Solder Hot Dip Tin (Sn) Terminal Finish
- Cathode Indicated By Polarity Band

DO-34



REF.	Millimeter	
	Min.	Max.
A	25.0	38.1
B	2.16	3.04
C	1.27	1.9
D	0.46	0.56



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Maximum Repetitive Reverse Voltage	V_{RRM}	250	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Non-repetitive Peak Forward Current Current	$I_{FM(\text{Surge})}$	1	A
		4	
Power Dissipation	P_D	300	mW
Junction, Storage Temperature	T_J, T_{STG}	150, -65~150	°C

Note:

1. These ratings are limiting values above which the serviceability of the diode may be impaired.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Min.	Max.	Unit	Test Condition
Breakdown Voltage	B_V	250	-	V	$I_R=100\mu\text{A}$
Leakage Current	I_R	-	10	μA	$V_R=220\text{V}$
Forward Voltage	V_F	-	1.5	V	$I_F=200\text{mA}$
Capacitance	C	-	5	pF	$V_R=0, f=1\text{MHz}$
Reverse Recovery Time	T_{RR}	-	50	nS	$I_F=I_R=30\text{mA}, I_{RR}=3\text{mA}, R_L=100\Omega$

CHARACTERISTIC CURVES

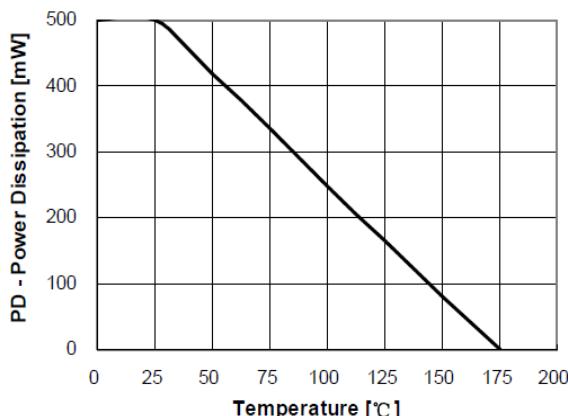


Figure 1. Power Dissipation vs Ambient Temperature
Valid provided leads at a distance of 0.8mm from case are kept at ambient temperature

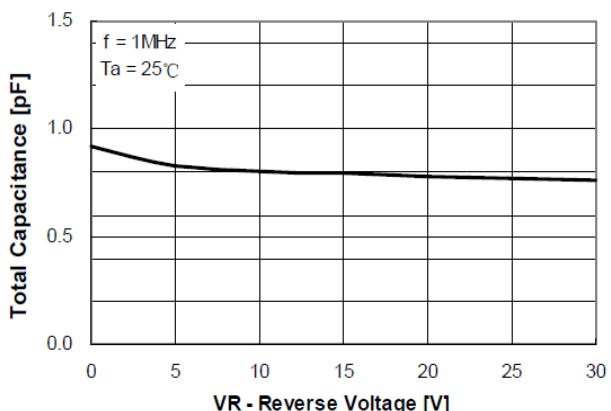


Figure 2. Total Capacitance

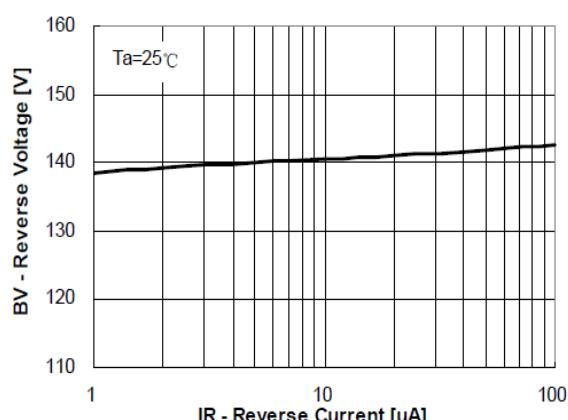


Figure 3. Reverse Voltage vs Reverse Current
BV – 1.0uA to 100uA

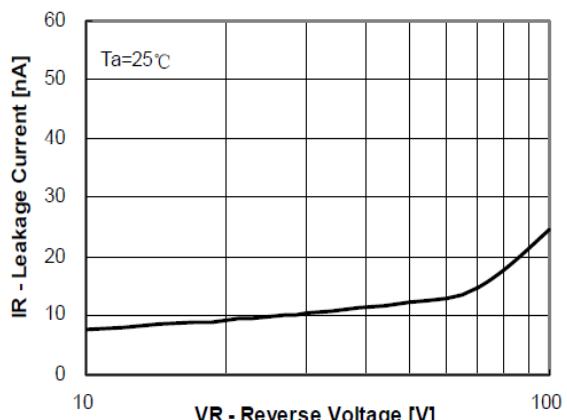


Figure 4. Reverse Current vs Reverse Voltage
IR – 10V to 100V

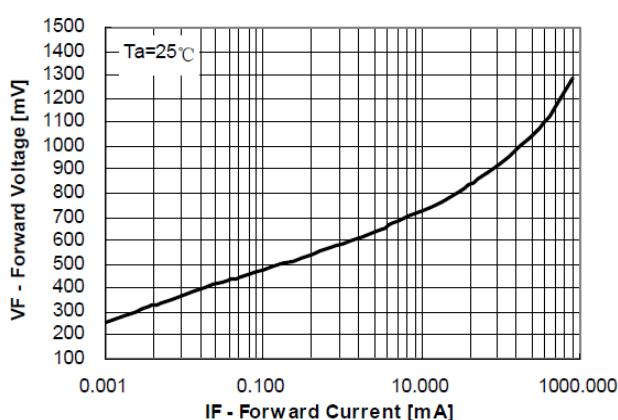


Figure 5. Forward Voltage vs Forward Current
VF – 0.001mA to 800mA

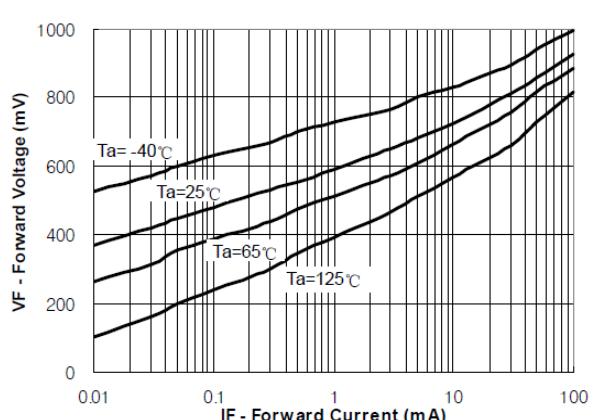


Figure 6. Forward Voltage vs Ambient Temperature
VF – 0.01mA to 100mA (-40 to +125 Deg C)